优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
30V	60mΩ @ V_{GS} = 8V	3.9A
	72mΩ @ V_{GS} = 4.5V	3.5A

Features and Benefits

- Low Q_g & Q_{gd}
- Small Footprint
- Low Profile 0.20mm Height

Description

This new generation MOSFET is designed to minimize the footprint in handheld and mobile application. The device can be used to replace many small signal MOSFETs with minimal footprint.

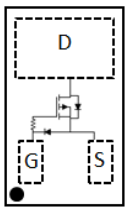
Applications

- Battery managements
- Load switches
- Battery protections
- Handheld and mobile applications

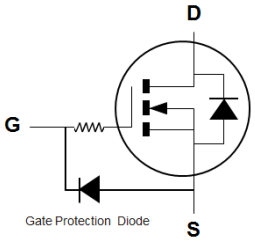
Mechanical Data

- Package: X4-DSN1006-3
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.00029 grams (Approximate)

X4-DSN1006-3



Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	12	V
Continuous Drain Current (Note 5) V_{GS} = 8V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.9 3.1	A
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.5 2.8	A
Pulsed Drain Current (Note 6)			I_{DM}	20	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P_D	0.79	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 7)	$R_{\theta JA}$	160	°C/W
Power Dissipation (Note 5)	P_D	1.35	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	93	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	100	nA	V_{DS} = 24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	50	nA	V_{GS} = 10V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.65	0.83	1.10	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	46	60	mΩ	V_{GS} = 8V, I_D = 0.5A
		—	52	72		V_{GS} = 4.5V, I_D = 0.5A
		—	69	110		V_{GS} = 2.5V, I_D = 0.5A
		—	101	160		V_{GS} = 1.8V, I_D = 0.5A
Diode Forward Voltage	V_{SD}	—	0.7	0.9	V	V_{GS} = 0V, I_S = 0.5A
Reverse Recovery Charge	Q_{RR}	—	2.4	—	nC	V_{DD} = 15V, I_F = 0.5A, di/dt = 300A/μs
Reverse Recovery Time	t_{RR}	—	7.1	—	ns	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	128	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	81	—		
Reverse Transfer Capacitance	C_{rss}	—	6.3	—		
Series Gate Resistance	R_g	—	20.9	—	Ω	f = 1MHz, V_{GS} = 0V, V_{DS} = 0V
Total Gate Charge	Q_g	—	1118	—	pC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 0.5A
Gate-Source Charge	Q_{gs}	—	163	—		
Gate-Drain Charge	Q_{gd}	—	241	—		
Gate Charge at V_{TH}	$Q_{g(TH)}$	—	130	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.3	—	ns	V_{DS} = 15V, V_{GS} = 4.5V, R_g = 2Ω, I_D = 0.5A
Turn-On Rise Time	t_R	—	2.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	12.9	—		
Turn-Off Fall Time	t_F	—	5.4	—		

Notes:
5. Device mounted on FR-4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.
6. Repetitive rating, pulse width limited by junction temperature.
7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

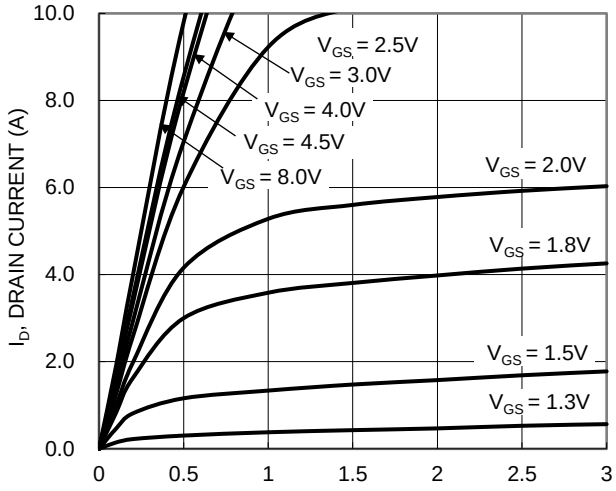


Figure 1. Typical Output Characteristic

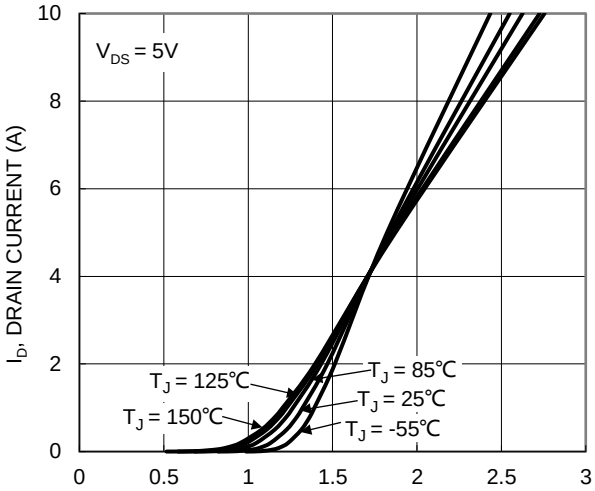


Figure 2. Typical Transfer Characteristic

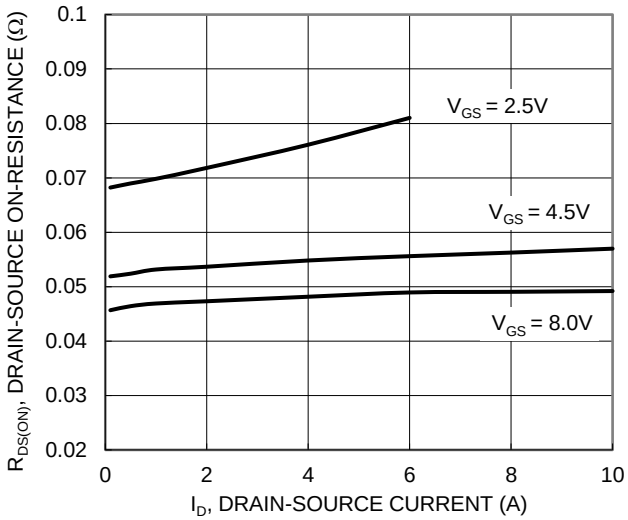


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

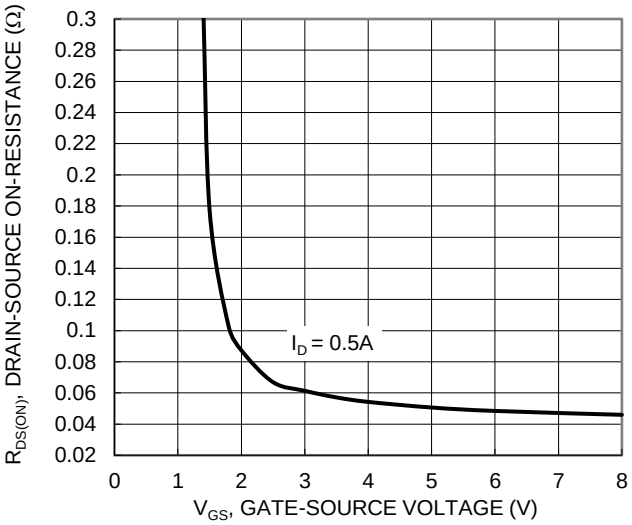


Figure 4. Typical Transfer Characteristic

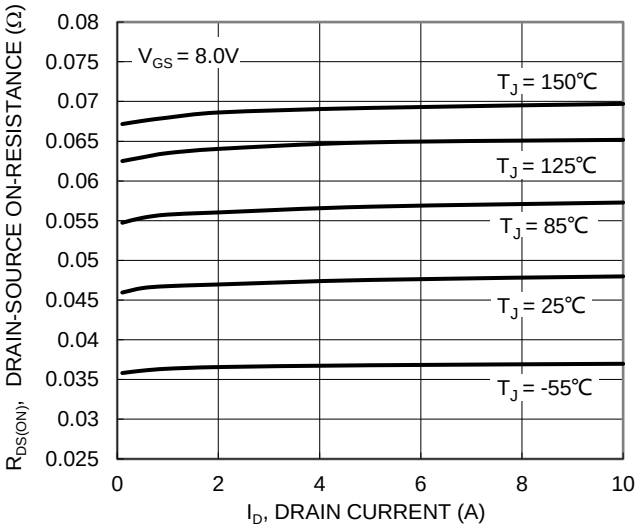


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

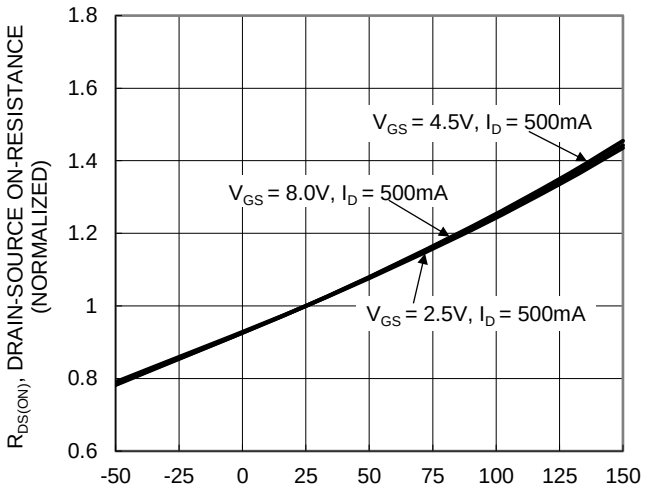


Figure 6. On-Resistance Variation with Junction Temperature

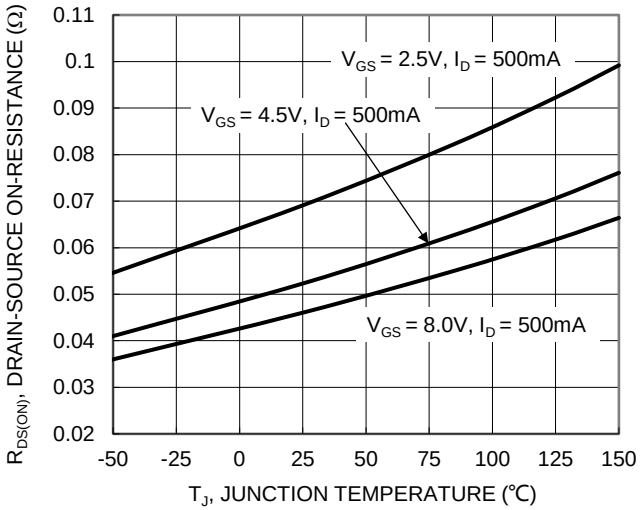


Figure 7. On-Resistance Variation with Junction Temperature

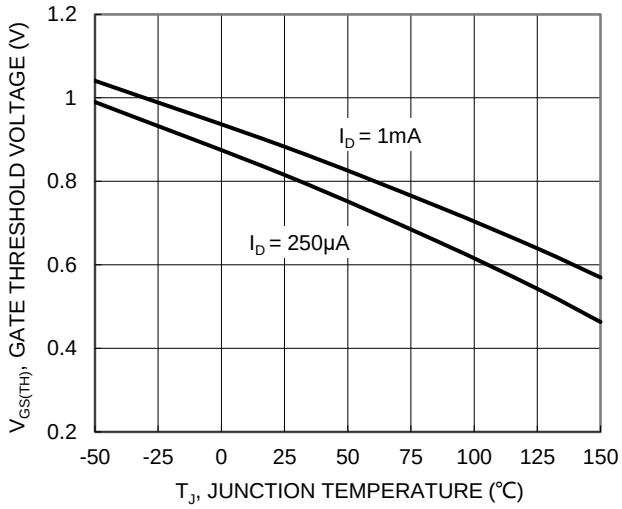


Figure 8. Gate Threshold Variation vs. Junction Temperature

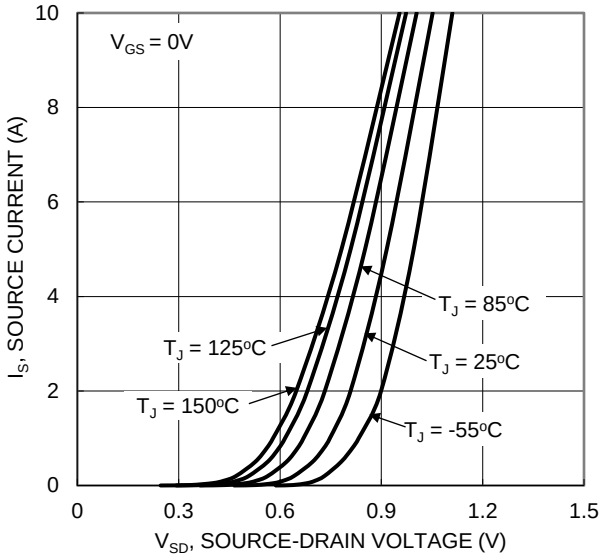


Figure 9. Diode Forward Voltage vs. Current

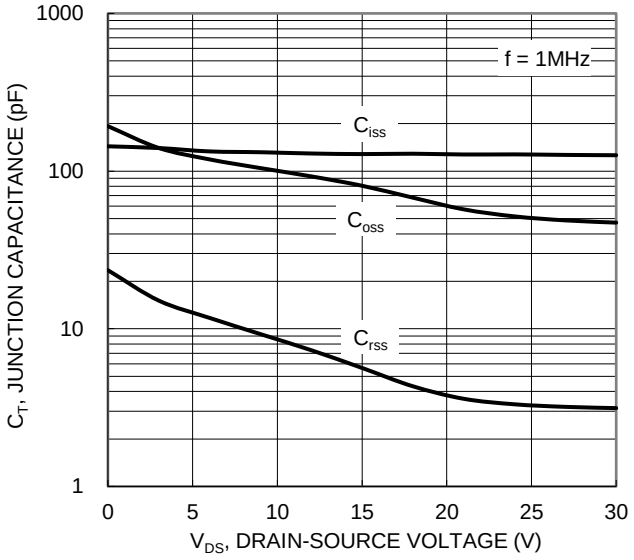


Figure 10. Typical Junction Capacitance

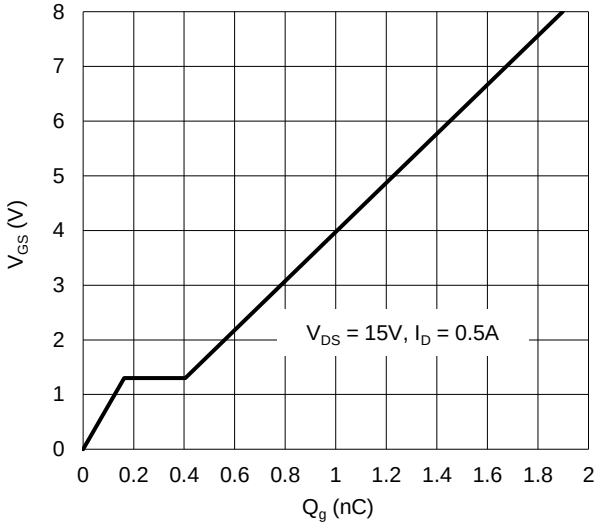


Figure 11. Gate Charge

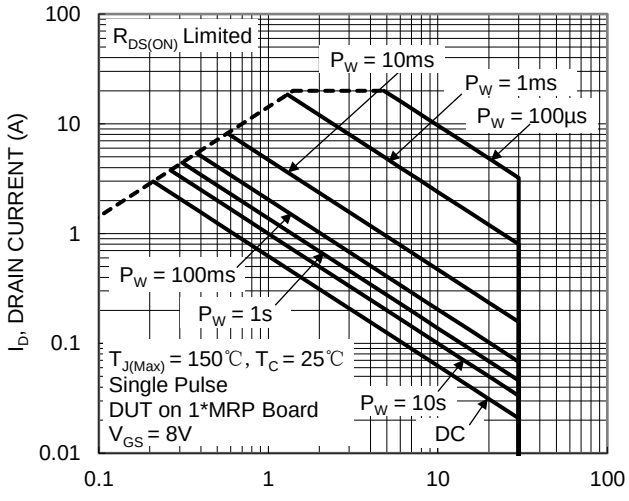


Figure 12. SOA, Safe Operation Area

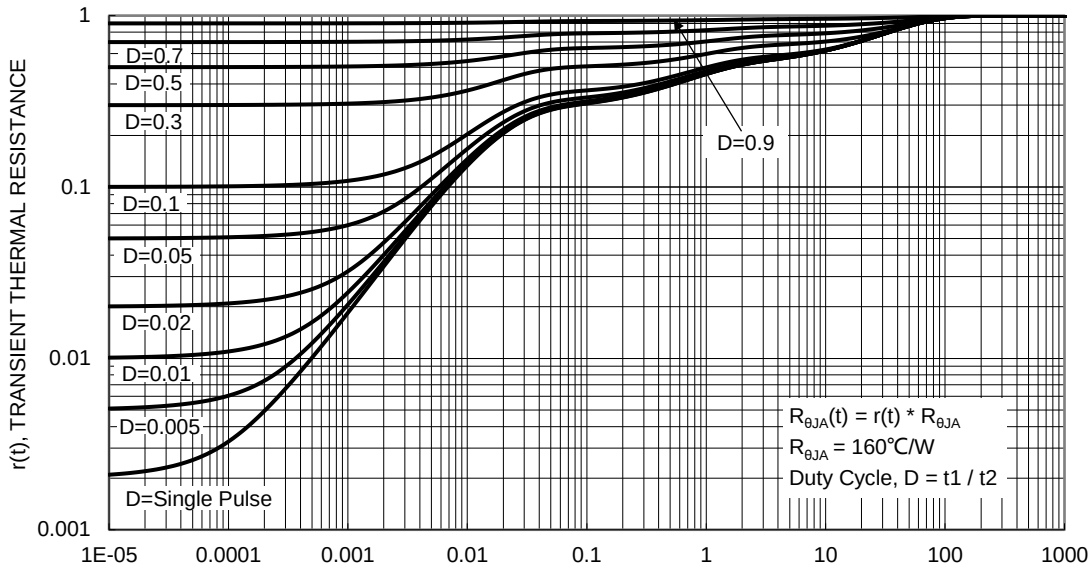
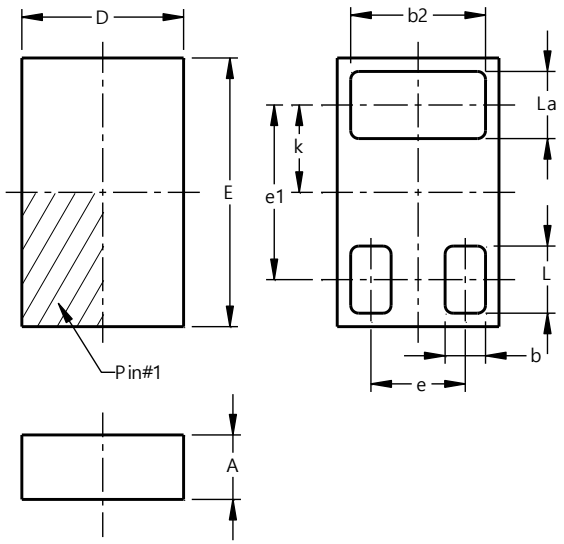


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

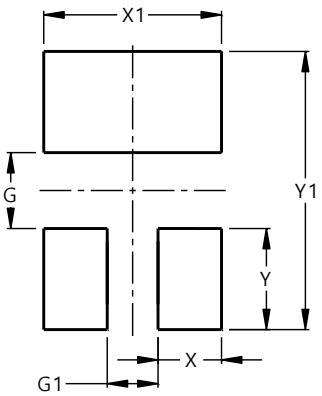
X4-DSN1006-3



X4-DSN1006-3			
Dim	**Min**	**Max**	**Typ**
A	0.18	0.22	0.20
b	0.14	0.16	0.15
b2	0.49	0.51	0.50
D	0.56	0.64	0.60
E	0.96	1.04	1.00
e	—	—	0.35
e1	—	—	0.65
k	—	—	0.325
L	0.24	0.26	0.25
La	0.24	0.26	0.25
All Dimensions in mm			

Suggested Pad Layout

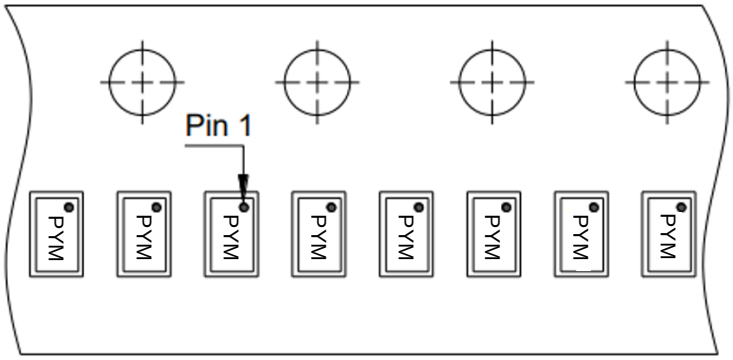
X4-DSN1006-3



Dimensions	Value (in mm)
G	0.40
G1	0.20
X	0.15
X1	0.50
Y	0.25
Y1	0.90

Tape and Reel Information

NK-DMN3060LCA3-7



NK-DMN3060LCA3-7A
Change the PIN1 orientation in the carrier tape, rotate 180 degree to meet customer demand (Top side).